

Yin Tang Yang

List of Publications by Year in descending order

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#	ARTICLE	IF	CITATIONS
1	DnRCNN: Deep Recurrent Convolutional Neural Network for HSI Destriping. IEEE Transactions on Neural Networks and Learning Systems, 2023, 34, 3255-3268.	7.2	10
2	A Fast Analysis Method of Multiphysics Coupling for 3-D Microsystem. IEEE Transactions on Computer-Aided Design of Integrated Circuits and Systems, 2022, 41, 2372-2379.	1.9	1
3	Adjustable Acoustic Field Controlled by "Ultrasonic Projector" on Ultrasound Application. IEEE Transactions on Ultrasonics, Ferroelectrics, and Frequency Control, 2022, 69, 254-260.	1.7	2
4	A 1V 3.5 μ W Bio-AFE With Chopper-Capacitor-Chopper Integrator-Based DSL and Low Power GM-C Filter. IEEE Transactions on Circuits and Systems II: Express Briefs, 2022, 69, 5-9.	2.2	9
5	Encrypted Data Retrieval and Sharing Scheme in Space-Air-Ground-Integrated Vehicular Networks. IEEE Internet of Things Journal, 2022, 9, 5957-5970.	5.5	5
6	Fast-switching SOI-LIGBT with compound dielectric buried layer and assistant-depletion trench. Chinese Physics B, 2022, 31, 047304.	0.7	0
7	A Miniatured Passive Low-Pass Filter With Ultrawide Stopband Based on 3-D Integration Technology. IEEE Microwave and Wireless Components Letters, 2022, 32, 29-32.	2.0	11
8	Optimization design of high-frequency ultrasonic transducer based on ANFIS and particle swarm optimization algorithm. Applied Acoustics, 2022, 187, 108507.	1.7	4
9	Complete Accumulation Lateral Double-Diffused MOSFET With Low ON-Resistance Applying Floating Buried Layer. IEEE Transactions on Electron Devices, 2022, 69, 658-663.	1.6	2
10	High-Frequency 0.36BiScO ₃ -0.64PbTiO ₃ Ultrasonic Transducer for High-Temperature Imaging Application. IEEE Transactions on Ultrasonics, Ferroelectrics, and Frequency Control, 2022, 69, 761-768.	1.7	7
11	A TSV-Based 3-D Electromagnetic Bandgap Structure on an Interposer for Noise Suppression. IEEE Transactions on Components, Packaging and Manufacturing Technology, 2022, 12, 147-154.	1.4	2
12	Study of Self-Heating and High-Power Microwave Effects for Enhancement-Mode p-Gate GaN HEMT. Micromachines, 2022, 13, 106.	1.4	12
13	A Survey on Analog-to-Digital Converter Integrated Circuits for Miniaturized High Resolution Ultrasonic Imaging System. Micromachines, 2022, 13, 114.	1.4	12
14	Novel low loss and snapback-free SOI LIGBT controlled by anode junction self-built potential. IEICE Electronics Express, 2022, 19, .	0.3	0
15	A Review of UltraHigh Frequency Ultrasonic Transducers. Frontiers in Materials, 2022, 8, .	1.2	11
16	Ultrawide Bandwidth High-Frequency Ultrasonic Transducers With Gradient Acoustic Impedance Matching Layer for Biomedical Imaging. IEEE Transactions on Ultrasonics, Ferroelectrics, and Frequency Control, 2022, 69, 1952-1959.	1.7	6
17	Novel anode Schottky trench contact controlled SOI LIGBT with low loss and snapback-free. IEICE Electronics Express, 2022, 19, 20220014-20220014.	0.3	0
18	Blockchain-based trust management for verifiable time synchronization service in IoT. Peer-to-Peer Networking and Applications, 2022, 15, 1152-1162.	2.6	2

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19	A new RFID ultra-lightweight authentication protocol for medical privacy protection in smart living. Computer Communications, 2022, 186, 121-132.	3.1	15
20	Novel Enhance-Mode AlGaIn/GaN JFET With BV of Over 1.2 kV Maintaining Low $R_{ON,sp}$. IEEE Transactions on Electron Devices, 2022, 69, 1200-1205.	1.6	5
21	Time-Domain Power Distribution Network (PDN) Analysis for 3-D Integrated Circuits Based on WLP-FDTD. IEEE Transactions on Components, Packaging and Manufacturing Technology, 2022, 12, 551-561.	1.4	3
22	Echo Signal Receiving and Data Conversion Integrated Circuits for Portable High-Frequency Ultrasonic Imaging System. IEEE Transactions on Ultrasonics, Ferroelectrics, and Frequency Control, 2022, 69, 1980-1993.	1.7	0
23	Two novel PSRR enhancement techniques for voltage reference of depletion NMOS. IEICE Electronics Express, 2022, , .	0.3	0
24	Optimization and Analysis of Microchannels Under Complex Power Distribution in 3-D ICs. IEEE Transactions on Components, Packaging and Manufacturing Technology, 2022, 12, 537-543.	1.4	2
25	Matching layer design of a 2 \times 2 piezo-composite ultrasonic transducer for biomedical imaging. Structural and Multidisciplinary Optimization, 2022, 65, 1.	1.7	2
26	A 2.5 V, 2.56 ppm/ $\text{\AA}^\circ\text{C}$ Curvature-Compensated Bandgap Reference for High-Precision Monitoring Applications. Micromachines, 2022, 13, 465.	1.4	1
27	Novel Step Floating Islands VDMOS with Low Specific on-Resistance by TCAD Simulation. Micromachines, 2022, 13, 573.	1.4	3
28	New Strained Lateral MOSFET With Ultralow On-Resistance by Surrounded Stress Dielectric Layer. IEEE Electron Device Letters, 2022, 43, 525-528.	2.2	4
29	High-Frequency Self-Focusing Ultrasonic Transducer With Piezoelectric Metamaterial. IEEE Electron Device Letters, 2022, 43, 946-949.	2.2	5
30	3-D Compact Marchand Balun Design Based on Through-Silicon via Technology for Monolithic and 3-D Integration. IEEE Transactions on Very Large Scale Integration (VLSI) Systems, 2022, 30, 1107-1118.	2.1	3
31	Compact Interdigital Bandpass Filter, Diplexer, and Triplexer Based on Through Quartz Vias (TQVs). IEEE Transactions on Components, Packaging and Manufacturing Technology, 2022, 12, 988-997.	1.4	2
32	Memory-Efficient Deformable Convolution Based Joint Denoising and Demosaicing for UHD Images. IEEE Transactions on Circuits and Systems for Video Technology, 2022, 32, 7346-7358.	5.6	11
33	Wide-Stopband Substrate Integrated Waveguide Filter Power Divider Based on Through Glass Quartz Via (TQV) Technology. IEEE Transactions on Components, Packaging and Manufacturing Technology, 2022, 12, 1196-1203.	1.4	4
34	Novel Si/SiC heterojunction lateral double-diffused metal oxide semiconductor field effect transistor with low specific on-resistance by super junction layer. , 2022, 168, 207298.		1
35	Joint Biological ID : A Secure and Efficient Lightweight Biometric Authentication Scheme. IEEE Transactions on Dependable and Secure Computing, 2022, , 1-16.	3.7	1
36	Cloud-based RFID mutual authentication scheme for efficient privacy preserving in IoV. Journal of the Franklin Institute, 2021, 358, 193-209.	1.9	23

#	ARTICLE	IF	CITATIONS
37	Liquid lens with adjustable focus for ultrasonic imaging. Applied Acoustics, 2021, 175, 107787.	1.7	20
38	Novel Si/SiC Heterojunction Lateral Double-Diffused Metal Oxide Semiconductor With SIPOS Field Plate by Simulation Study. IEEE Journal of the Electron Devices Society, 2021, 9, 114-120.	1.2	12
39	Compact Bandpass Filter and Diplexer With Wide-Stopband Suppression Based on Balanced Substrate-Integrated Waveguide. IEEE Transactions on Microwave Theory and Techniques, 2021, 69, 54-64.	2.9	33
40	Model for Rapidly Computing the Highest Temperature Based on Fermat Point in Chips. Journal of Thermophysics and Heat Transfer, 2021, 35, 92-97.	0.9	0
41	Novel Low Loss LIGBT With Assisted Depletion N-Region and P-Buried Layer. IEEE Journal of the Electron Devices Society, 2021, 9, 409-414.	1.2	2
42	An Efficient Optimization Design for 1 MHz Ultrasonic Transmitting Transducer. IEEE Sensors Journal, 2021, 21, 7420-7427.	2.4	10
43	Acoustic Hole-Hologram for Ultrasonic Focusing With High Sensitivity. IEEE Sensors Journal, 2021, 21, 8935-8942.	2.4	6
44	Experimental of Folded Accumulation Lateral Double-diffused Transistor with Low Specific On Resistance. , 2021, , .		4
45	Accumulation-Mode Lateral Double-Diffused MOSFET Breaking Silicon Limit by Eliminating Dependence of Specific ON-Resistance on Doping Concentration. IEEE Transactions on Electron Devices, 2021, 68, 2414-2419.	1.6	4
46	Novel Snapback-Free SOI LIGBT With Shorted Anode and Trench Barriers. IEEE Transactions on Electron Devices, 2021, 68, 2408-2413.	1.6	18
47	An Efficient Optimization Design of Liquid Lens for Acoustic Pattern Control. IEEE Transactions on Ultrasonics, Ferroelectrics, and Frequency Control, 2021, 68, 1546-1554.	1.7	7
48	Experimental Results for AlGaN/GaN HEMTs Improving Breakdown Voltage and Output Current by Electric Field Modulation. IEEE Transactions on Electron Devices, 2021, 68, 2240-2245.	1.6	17
49	Optimization Design of Ultrasonic Transducer With Multimatching Layer. IEEE Transactions on Ultrasonics, Ferroelectrics, and Frequency Control, 2021, 68, 2202-2211.	1.7	13
50	Intelligent Optimization of Matching Layers for Piezoelectric Ultrasonic Transducer. IEEE Sensors Journal, 2021, 21, 13107-13115.	2.4	8
51	New Strained Silicon-On-Insulator Lateral MOSFET With Ultralow ON-Resistance by $\text{Si}_{1-x}\text{Ge}_x$ -P-Top Layer and Trench Gate. IEEE Electron Device Letters, 2021, 42, 788-791.	2.2	3
52	Recent Development and Perspectives of Optimization Design Methods for Piezoelectric Ultrasonic Transducers. Micromachines, 2021, 12, 779.	1.4	15
53	Research on the leakage current at sidewall of mesa Ge/Si avalanche photodiode. AIP Advances, 2021, 11, 075320.	0.6	2
54	Novel SOI LDMOS Without RESURF Effect by Flexible Substrate for Flexible Electronic Systems. IEEE Transactions on Electron Devices, 2021, 68, 4150-4155.	1.6	5

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55	Focus of ultrasonic underwater sound with 3D printed phononic crystal. Applied Physics Letters, 2021, 119, .	1.5	15
56	Multilayer Stairstep Piezoelectric Structure Design for Ultrabroad-Bandwidth Ultrasonic Transducer. IEEE Sensors Journal, 2021, 21, 19889-19895.	2.4	11
57	Mechanism Analysis and Thermal Damage Prediction of High-Power Microwave Radiated CMOS Circuits. IEEE Transactions on Device and Materials Reliability, 2021, 21, 444-451.	1.5	3
58	Anonymous and Privacy-Preserving Federated Learning With Industrial Big Data. IEEE Transactions on Industrial Informatics, 2021, 17, 6314-6323.	7.2	69
59	Compact and Physics-Based Modeling of 3-D Inductor Based on Through Silicon Via. IEEE Electron Device Letters, 2021, 42, 1559-1562.	2.2	6
60	Novel Vertical Power MOSFET With Step Hk Insulator Close to Super Junction Limit Relationship Between Breakdown Voltage and Specific ON-Resistance by Improving Electric Field Modulation. IEEE Transactions on Electron Devices, 2021, 68, 5048-5054.	1.6	3
61	The forbidden band and size selectivity of acoustic radiation force trapping. IScience, 2021, 24, 101988.	1.9	15
62	Electrothermal coupling analysis of 3D Integrated Micro System Based on dual cell method. Wuli Xuebao/Acta Physica Sinica, 2021, .	0.2	1
63	Intelligent optimization design of 2D piezo-composites for ultrasonic transducer. Sensors and Actuators A: Physical, 2021, 332, 113171.	2.0	0
64	An Anisotropic Equivalent Thermal Model for Shield Differential Through-Silicon Vias. Micromachines, 2021, 12, 1223.	1.4	6
65	Numerical Modelling of Interconnect Electromigration Under Non-DC Stressing Conditions. IETE Journal of Research, 2020, 66, 85-90.	1.8	0
66	The Analysis Model of AlGaN/GaN HEMTs with Electric Field Modulation Effect. IETE Technical Review (Institution of Electronics and Telecommunication Engineers, India), 2020, 37, 553-564.	2.1	2
67	SRNoC: An Ultra-Fast Configurable FPGA-Based NoC Simulator Using Switch Router Architecture. IEEE Transactions on Computer-Aided Design of Integrated Circuits and Systems, 2020, 39, 2798-2811.	1.9	6
68	High Resolution ADC for Ultrasound Color Doppler Imaging Based on MASH Sigma-Delta Modulator. IEEE Transactions on Biomedical Engineering, 2020, 67, 1438-1449.	2.5	8
69	Multi-layer polymer-metal structures for acoustic impedance matching in high-frequency broadband ultrasonic transducers design. Applied Acoustics, 2020, 160, 107123.	1.7	30
70	A Handheld Nano Through-Wall Radar Locating With the Gain-Enhanced Vivaldi Antenna. IEEE Sensors Journal, 2020, 20, 4420-4429.	2.4	11
71	Novel Lateral Double-Diffused MOSFET With Ultralow On-Resistance by the Variable Resistivity of Drift Region. IEEE Electron Device Letters, 2020, 41, 1681-1684.	2.2	16
72	Novel Power MOSFET With Partial SiC/Si Heterojunction to Improve Breakdown Voltage by Breakdown Point Transfer (BPT) Terminal Technology. IEEE Journal of the Electron Devices Society, 2020, 8, 559-564.	1.2	3

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73	Unified Analytical Model for SOI LDMOS With Electric Field Modulation. IEEE Journal of the Electron Devices Society, 2020, 8, 686-694.	1.2	6
74	Particle Swarm Optimization Algorithm-Based Design Method for Ultrasonic Transducers. Micromachines, 2020, 11, 715.	1.4	31
75	Simulation Study on Dynamic and Static Characteristics of Novel SiC Gate-Controlled Bipolar-Field-Effect Composite Transistor. IEEE Journal of the Electron Devices Society, 2020, 8, 1082-1088.	1.2	4
76	Mechanism of AlGaAs/InGaAs pHEMT Nonlinear Response Under High-Power Microwave Radiation. IEEE Journal of the Electron Devices Society, 2020, 8, 731-737.	1.2	9
77	New Strained LDMOS With Ultralow ON-Resistance by Si ¹ y C y Source Stressor for About 20 V Low-Voltage Applications. IEEE Transactions on Electron Devices, 2020, 67, 4998-5004.	1.6	5
78	A Collaborative Auditing Blockchain for Trustworthy Data Integrity in Cloud Storage System. IEEE Access, 2020, 8, 94780-94794.	2.6	40
79	ACâ€šJ VDMOS with ultraâ€šlow resistance. Micro and Nano Letters, 2020, 15, 230-233.	0.6	4
80	A breakdown model of LDMOS optimizing lateral and vertical electric field to improve breakdown voltage by multi-ring technology. Solid-State Electronics, 2020, 166, 107775.	0.8	4
81	Accumulation-Mode Device: New Power MOSFET Breaking Superjunction Silicon Limit by Simulation Study. IEEE Transactions on Electron Devices, 2020, 67, 1085-1089.	1.6	8
82	An optimization design strategy of 1â€š3 piezocomposite ultrasonic transducer for imaging applications. Materials Today Communications, 2020, 24, 100991.	0.9	28
83	Design of a Si-based Lattice-matched GeSn/SiGeSn Multi-quantum-well Laser. Journal of Russian Laser Research, 2020, 41, 98-103.	0.3	0
84	Novel SOI LIGBT with fastâ€šswitching by the electric field modulation. Micro and Nano Letters, 2020, 15, 155-158.	0.6	2
85	A Secure and Verifiable Data Sharing Scheme Based on Blockchain in Vehicular Social Networks. IEEE Transactions on Vehicular Technology, 2020, 69, 5826-5835.	3.9	96
86	First-Principles Study on Structural, Mechanical, Anisotropic, Electronic and Thermal Properties of III-Phosphides: XP (X = Al, Ga, or In) in the P6422 Phase. Materials, 2020, 13, 686.	1.3	11
87	Thermal Field Analysis for New AlGaN/GaN HEMT With Partial Etched AlGaN Layer. IEEE Journal of the Electron Devices Society, 2020, 8, 442-447.	1.2	1
88	Penta-C20: A Superhard Direct Band Gap Carbon Allotrope Composed of Carbon Pentagon. Materials, 2020, 13, 1926.	1.3	31
89	High frequency needle ultrasonic transducers based on Mn doped piezoelectric single crystal. Journal of Alloys and Compounds, 2020, 832, 154951.	2.8	17
90	Dynamic back-off chain-building scheme based on network state partition. Optical Engineering, 2020, 59, .	0.5	0

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91	Physics based scalable inductance model for three-dimensional solenoid inductors. <i>Microelectronics Journal</i> , 2020, 103, 104867.	1.1	1
92	Balanced SIW BPF based on Through-Glass Vias. , 2020, , .		0
93	Thermal-Aware Modeling and Analysis for a Power Distribution Network Including Through-Silicon-Vias in 3-D ICs. <i>IEEE Transactions on Computer-Aided Design of Integrated Circuits and Systems</i> , 2019, 38, 1278-1290.	1.9	9
94	A 1.2-V 2.41-GHz Three-Stage CMOS OTA With Efficient Frequency Compensation Technique. <i>IEEE Transactions on Circuits and Systems I: Regular Papers</i> , 2019, 66, 20-30.	3.5	28
95	Analysis of the Coupling Capacitance Between TSVs and Adjacent RDL Interconnections. <i>IEEE Transactions on Electromagnetic Compatibility</i> , 2019, 61, 512-520.	1.4	3
96	Analysis of the Fast-Switching LIGBT With Double Gates and Integrated Schottky Barrier Diode. <i>IEEE Transactions on Electron Devices</i> , 2019, 66, 2675-2680.	1.6	15
97	Analytical model of buried air partial SOI LDMOS. <i>Superlattices and Microstructures</i> , 2019, 132, 106162.	1.4	4
98	Fast-Switching Lateral IGBT with Trench/Planar Gate and Integrated Schottky Barrier Diode (SBD). , 2019, , .		9
99	New Super-Junction LDMOS Breaking Silicon Limit by Multi-Ring Assisted Depletion Substrate. <i>IEEE Transactions on Electron Devices</i> , 2019, 66, 4836-4841.	1.6	19
100	Novel Superjunction LDMOS With a High- κ Dielectric Trench by TCAD Simulation Study. <i>IEEE Transactions on Electron Devices</i> , 2019, 66, 2327-2332.	1.6	23
101	Vertical double diffused MOSFET with step HK insulator improving electric field modulation. <i>Micro and Nano Letters</i> , 2019, 14, 219-222.	0.6	4
102	An Effective Approach for Thermal Performance Analysis of 3-D Integrated Circuits With Through-Silicon Vias. <i>IEEE Transactions on Components, Packaging and Manufacturing Technology</i> , 2019, 9, 877-887.	1.4	19
103	TAONoC: A Regular Passive Optical Network-on-Chip Architecture Based on Comb Switches. <i>IEEE Transactions on Very Large Scale Integration (VLSI) Systems</i> , 2019, 27, 954-963.	2.1	20
104	Wideband Electromagnetic Distribution Characterization and Dielectric Analysis of Shielded-Pair Through-Silicon Via Using Recursive Approximation Algorithm. <i>IEEE Transactions on Components, Packaging and Manufacturing Technology</i> , 2019, 9, 936-944.	1.4	1
105	Nonlinear Electrothermal Model for Investigating Transient Temperature Responses of a Through-Silicon Via Array Applied With Gaussian Pulses in 3-D IC. <i>IEEE Transactions on Electron Devices</i> , 2019, 66, 1032-1040.	1.6	10
106	A Group-Based Laser Power Supply Scheme for Photonic Network on Chip. <i>IEEE Photonics Journal</i> , 2019, 11, 1-14.	1.0	1
107	Fabrication and Characterization of High-Sensitivity Ultrasonic Transducers With Functionally Graded Design. <i>IEEE Sensors Journal</i> , 2019, 19, 6650-6654.	2.4	20
108	Noise Characteristics of MgZnO-Based Metal-Semiconductor-Metal Photodetector. <i>IEEE Transactions on Electron Devices</i> , 2019, 66, 983-990.	1.6	3

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109	Si/SiC heterojunction lateral double-gate diffused metal oxide semiconductor field effect transistor with breakdown point transfer (BPT) terminal technology. <i>Micro and Nano Letters</i> , 2019, 14, 1092-1095.	0.6	7
110	Dynamic determination method of spinning reserve capacity based on situation awareness of power systems. , 2019, , .		0
111	An Efficient Multi-Message and Multi-Receiver Signcrypton Scheme for Heterogeneous Smart Mobile IoT. <i>IEEE Access</i> , 2019, 7, 180205-180217.	2.6	27
112	SiC gate-controlled bipolar field-effect composite transistor with large on-state current. <i>Micro and Nano Letters</i> , 2019, 14, 1406-1409.	0.6	1
113	A 4.6-ppm/Å°C High-Order Curvature Compensated Bandgap Reference for BMIC. <i>IEEE Transactions on Circuits and Systems II: Express Briefs</i> , 2019, 66, 1492-1496.	2.2	27
114	Ultra-Compact TSV-Based L-C Low-Pass Filter With Stopband Up to 40 GHz for Microwave Application. <i>IEEE Transactions on Microwave Theory and Techniques</i> , 2019, 67, 738-745.	2.9	49
115	Wideband Substrate Integrated Waveguide Bandpass Filter Based on 3-D ICs. <i>IEEE Transactions on Components, Packaging and Manufacturing Technology</i> , 2019, 9, 728-735.	1.4	36
116	Permutation Matrix Encryption Based Ultralightweight Secure RFID Scheme in Internet of Vehicles. <i>Sensors</i> , 2019, 19, 152.	2.1	14
117	Blockchain-Based Secure Time Protection Scheme in IoT. <i>IEEE Internet of Things Journal</i> , 2019, 6, 4671-4679.	5.5	51
118	Breakdown Mechanisms of Power Semiconductor Devices. <i>IETE Technical Review (Institution of Tj ETQq0 0 0 rgBT /Overlock 10 Tf 50 3</i>	2.1	13
119	A 10-Bit 600-MS/s Time-Interleaved SAR ADC With Interpolation-Based Timing Skew Calibration. <i>IEEE Transactions on Circuits and Systems II: Express Briefs</i> , 2019, 66, 16-20.	2.2	22
120	Wideband Fourth-Harmonic Mixer Operated at 325-500 GHz. <i>IEEE Microwave and Wireless Components Letters</i> , 2018, 28, 242-244.	2.0	19
121	First-principles investigations on structural, elastic and mechanical properties of BNxAs1-x ternary alloys. <i>International Journal of Modern Physics B</i> , 2018, 32, 1850152.	1.0	1
122	0.36BiScO3-0.64PbTiO3 piezoelectric ceramics for high temperature ultrasonic transducer applications. <i>Journal of Alloys and Compounds</i> , 2018, 743, 365-371.	2.8	28
123	Wideband Electromagnetic Model and Analysis of Shielded-Pair Through-Silicon Vias. <i>IEEE Transactions on Components, Packaging and Manufacturing Technology</i> , 2018, 8, 473-481.	1.4	15
124	Lightweight RFID Protocol for Medical Privacy Protection in IoT. <i>IEEE Transactions on Industrial Informatics</i> , 2018, 14, 1656-1665.	7.2	135
125	Theory Analyses of SJ-LDMOS With Multiple Floating Buried Layers Based on Bulk Electric Field Modulation. <i>IEEE Transactions on Electron Devices</i> , 2018, 65, 2565-2572.	1.6	13
126	A first principle calculation of anisotropic elastic, mechanical and electronic properties of TiB. <i>AIP Conference Proceedings</i> , 2018, , .	0.3	0

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127	Theoretical investigations of Ge _{1-x} Sn _x alloys (x=0, 0.333, 0.667, 1) in P42/ncm phase. Journal of Materials Science, 2018, 53, 9611-9626.	1.7	26
128	Blockchain-based efficient privacy preserving and data sharing scheme of content-centric network in 5G. IET Communications, 2018, 12, 527-532.	1.5	120
129	Application of Novel Terminal Technologies for Superjunction Power MOSFETs. IETE Technical Review (Institution of Electronics and Telecommunication Engineers, India), 2018, 35, 402-412.	2.1	1
130	Secure ultra-lightweight RFID mutual authentication protocol based on transparent computing for IoT. Peer-to-Peer Networking and Applications, 2018, 11, 723-734.	2.6	13
131	Secure, efficient and revocable data sharing scheme for vehicular fogs. Peer-to-Peer Networking and Applications, 2018, 11, 766-777.	2.6	23
132	Secure and private key management scheme in big data networking. Peer-to-Peer Networking and Applications, 2018, 11, 992-999.	2.6	4
133	Theoretical investigations of group IV alloys in the Lonsdaleite phase. Journal of Materials Science, 2018, 53, 2785-2801.	1.7	31
134	A 1.4-mW 10-Bit 150-MS/s SAR ADC With Nonbinary Split Capacitive DAC in 65-nm CMOS. IEEE Transactions on Circuits and Systems II: Express Briefs, 2018, 65, 1524-1528.	2.2	29
135	A Background Timing Skew Calibration Technique in Time-Interleaved ADCs With Second Order Compensation. , 2018, , .		5
136	Evaluation of Frequency Regulation Capability of Wind Power Considering its Uncertainty. , 2018, , .		1
137	Frequency Emergency Control Strategy Considering the Operation Speed of Frequency Regulation resources. , 2018, , .		2
138	Analysis of the novel Snapback-Free LIGBT with fast-switching and improved latch-up immunity by TCAD Simulation. IEEE Electron Device Letters, 2018, , 1-1.	2.2	18
139	H OEIN: A Hierarchical Hybrid Optical/Electrical Interconnection Network for Exascale Computing Systems. IEEE Transactions on Multi-Scale Computing Systems, 2018, 4, 722-733.	2.5	0
140	3D numerical simulations of single-event transient effects in SOI FinFETs. Journal of Computational Electronics, 2018, 17, 1608-1614.	1.3	5
141	Fabrication of PMN-PT/Epoxy 2 nd Composite Ultrasonic Transducers and Analysis Based on Equivalent Circuit Model. Journal of Electronic Materials, 2018, 47, 6842-6847.	1.0	21
142	Interfacial electromagnetic-thermal characterization of a shielded pair through-silicon via a silicon interposer. Semiconductor Science and Technology, 2018, 33, 115022.	1.0	0
143	Accurate Inductance Modeling of 3-D Inductor Based on TSV. IEEE Microwave and Wireless Components Letters, 2018, 28, 900-902.	2.0	13
144	EARS-DM: Efficient Auto Correction Retrieval Scheme for Data Management in Edge Computing. Sensors, 2018, 18, 3616.	2.1	5

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145	Electronic and elastic properties of the antiferroelectric structure Mg ₂ Si under pressure. AIP Conference Proceedings, 2018, , .	0.3	1
146	Novel lateral double-diffused MOSFET with folded silicon and high-permittivity dielectric breaking silicon limit. Superlattices and Microstructures, 2018, 123, 280-285.	1.4	3
147	SiC/Si heterojunction VDMOS breaking silicon limit by breakdown point transfer technology. Micro and Nano Letters, 2018, 13, 96-99.	0.6	16
148	Novel SiC/Si Heterojunction Power MOSFET With Breakdown Point Transfer Terminal Technology by TCAD Simulation Study. IEEE Transactions on Electron Devices, 2018, 65, 3388-3393.	1.6	22
149	Analysis of the novel Si/SiC heterojunction IGBT characteristics by TCAD simulation. Superlattices and Microstructures, 2018, 122, 631-635.	1.4	3
150	Structural, Mechanical, Anisotropic, and Thermal Properties of AIAs in oC12 and hP6 Phases under Pressure. Materials, 2018, 11, 740.	1.3	12
151	Novel LDMOS Optimizing Lateral and Vertical Electric Field to Improve Breakdown Voltage by Multi-Ring Technology. IEEE Electron Device Letters, 2018, 39, 1358-1361.	2.2	27
152	Structural, Electronic, and Thermodynamic Properties of Tetragonal t-SixGe3âˆ™xN4. Materials, 2018, 11, 397.	1.3	7
153	Etched Al 0.32 Ga 0.68 N/GaN HEMTs with high output current and breakdown voltage (>600 V). Micro and Nano Letters, 2018, 13, 676-679.	0.6	4
154	A 140â€“220-GHz Balanced Doubler With 8.7%â€“12.7% Efficiency. IEEE Microwave and Wireless Components Letters, 2018, 28, 515-517.	2.0	10
155	An ultra-lightweight RFID authentication scheme for mobile commerce. Peer-to-Peer Networking and Applications, 2017, 10, 368-376.	2.6	35
156	Electromechanical modeling of stretchable interconnects. Journal of Computational Electronics, 2017, 16, 202-209.	1.3	7
157	A Superjunction U-MOSFET With SIPOS Pillar Breaking Superjunction Silicon Limit by TCAD Simulation Study. IEEE Electron Device Letters, 2017, 38, 794-797.	2.2	19
158	Proxy-assisted access control scheme of cloud data for smart cities. Personal and Ubiquitous Computing, 2017, 21, 937-947.	1.9	6
159	Enhancementâ€mode AlGaIn/GaN HEMTs with optimised electric field using a partial GaN cap layer. Micro and Nano Letters, 2017, 12, 763-766.	0.6	13
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